HALOGEN

FREE

Vishay Siliconix

N-Channel 60 V (D-S) MOSFET

SOT-23 (TO-236)



Marking code: 7K

PRODUCT SUMMARY					
V _{DS} (V)	60				
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10 \text{ V}$	2				
Q _g typ. (nC)	0.4				
I _D (mA)	300				
Configuration	Single				

FEATURES

Low on-resistance: 2 Ω
Low threshold: 2 V (typ.)

Low input capacitance: 25 pFFast switching speed: 25 ns

Low input and output leakage

TrenchFET® power MOSFET

• 2000 V ESD protection

Material estagarization for definition

 Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

Note

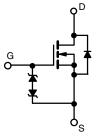
This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

BENEFITS

- · Low offset voltage
- Low voltage operation
- Easily driven without buffer
- · High speed circuits
- · Low error voltage

APPLICATIONS

- Direct logic-level interface: TTL/CMOS
- Drivers: relays, solenoids, lamps, hammers, display, memories, transistors, etc.
- · Battery operated systems
- Solid state relays



N-Channel MOSFET

ORDERING INFORMATION				
Package	SOT-23			
Lead (Pb)-free	2N7002K-T1-E3			
Lead (Pb)-free and halogen-free	2N7002K-T1-GE3			

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V_{DS}	60	V	
Gate-source voltage		V_{GS}	± 20	V	
Continuous drain ourrent (T = 150 °C) h	T _A = 25 °C	- I _D	300	mA	
Continuous drain current (T _J = 150 °C) ^b	T _A = 100 °C		190		
Pulsed drain current ^a		I _{DM}	800		
Power dissipation ^b	T _A = 25 °C	В	0.35	W	
Power dissipation •	T _A = 100 °C	- P _D	0.14		
Maximum junction-to-ambient ^b		R _{thJA}	350	°C/W	
Operating junction and storage temperature range		T _{J,} T _{stg}	-55 to +150	°C	

Notes

- a. Pulse width limited by maximum junction temperature
- b. Surface mounted on FR4 board

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PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS				
PARAMETER	STIMBOL	TEST CONDITIONS	MIN.	TYP. a	MAX.	UNIT	
Static							
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 10 \mu\text{A}$	60	-	-	V	
Gate-threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	1	-	2.5	V	
		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 10		
		$V_{DS} = 0 V$, $V_{GS} = \pm 15 V$	-	-	1	μA	
Gate-body leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}$	-	-	± 150	,	
		V _{DS} = 0 V, V _{GS} = ± 10 V, T _J = 85 °C	-	-	± 1000	nA	
		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 5 \text{ V}$	-	-	± 100	1	
Zero gate voltage drain current		V _{DS} = 60 V, V _{GS} = 0 V	-	-	1	μА	
	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V, T _J = 125 °C	-	-	500		
On-state drain current ^b		V _{GS} = 10 V, V _{DS} = 7.5 V	800	-	-	mA	
	I _{D(on)}	V _{GS} = 4.5 V, V _{DS} = 10 V	500	-	-		
Drain-source on-resistance b	Б	V _{GS} = 10 V, I _D = 500 mA	-	-	2	Ω	
	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 200 \text{ mA}$	-	-	4		
Forward transconductance b	9 _{fs}	V _{DS} = 10 V, I _D = 200 mA	100	-	-	mS	
Diode forward voltage	V _{SD}	I _S = 200 mA, V _{GS} = 0 V	-	-	1.3	V	
Dynamic ^{a, b}	<u>.</u>						
Total gate charge	Qg	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}$ $I_D \cong 250 \text{ mA}$	-	0.4	0.6	nC	
Input capacitance	C _{iss}		-	30	-		
Output capacitance	C _{oss}	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}$ f = 1 MHz	-	6	=	pF	
Reverse transfer capacitance	C _{rss}	I = I IVII IZ	-	2.5	-		
Switching ^{a, c}	,				L		
Turn-on time	t _{d(on)}	$V_{DD} = 30 \text{ V}, R_{L} = 150 \Omega$	-	-	25	ns	
Turn-off time	t _{d(off)}	$I_D \cong 200 \text{ mA}, V_{GEN} = 10 \text{ V}, R_g = 10 \Omega$	-	-	35		

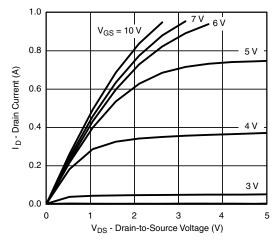
Notes

- a. For DESIGN AID ONLY, not subject to production testing
- b. Pulse test: pulse width \leq 300 μ s duty cycle \leq 2 %
- c. Switching time is essentially independent of operating temperature

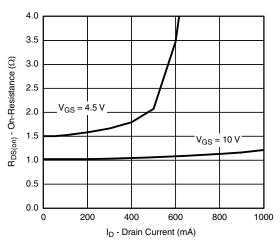
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



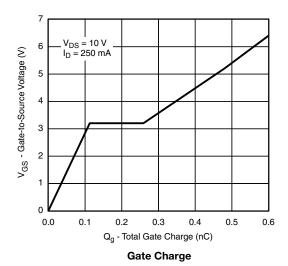
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

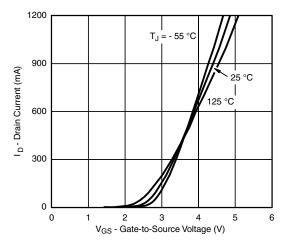


Output Characteristics

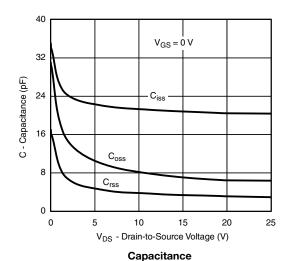


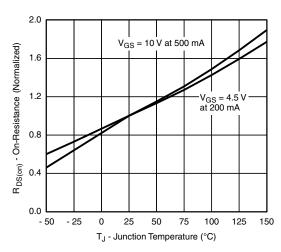
On-Resistance vs. Drain Current





Transfer Characteristics

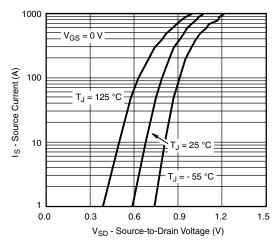




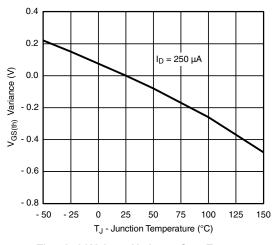
On-Resistance vs. Junction Temperature



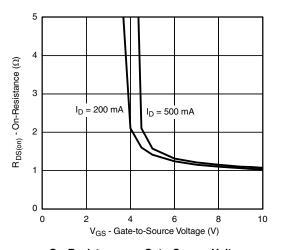
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



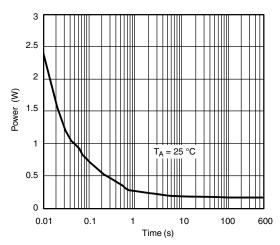
Source-Drain Diode Forward Voltage



Threshold Voltage Variance Over Temperature



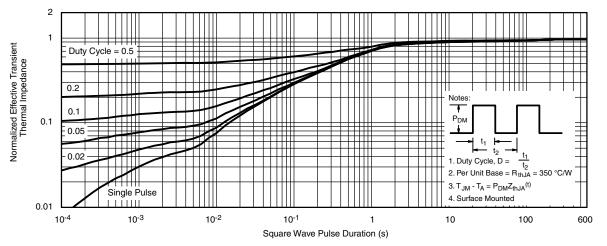
On-Resistance vs. Gate-Source Voltage



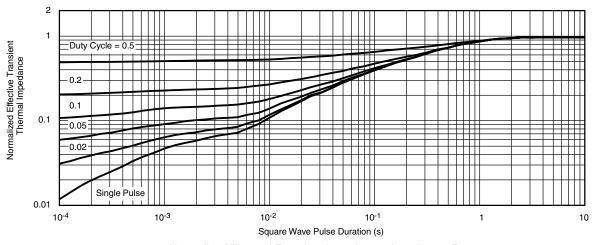
Single Pulse Power, Junction-to-Ambient



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?71333.

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SOT-23 (TO-236): 3-LEAD







Dim	MILLIMETERS		INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
FCN: S-03946-Rev K 09-	lul-01	•			

ECN: S-03946-Rev. K, 09-Jul-01

DWG: 5479

Document Number: 71196 www.vishay.com 09-Jul-01





Mounting LITTLE FOOT® SOT-23 Power MOSFETs

Wharton McDaniel

Surface-mounted LITTLE FOOT power MOSFETs use integrated circuit and small-signal packages which have been been modified to provide the heat transfer capabilities required by power devices. Leadframe materials and design, molding compounds, and die attach materials have been changed, while the footprint of the packages remains the same.

See Application Note 826, Recommended Minimum Pad Patterns With Outline Drawing Access for Vishay Siliconix MOSFETs, (http://www.vishay.com/doc?72286), for the basis of the pad design for a LITTLE FOOT SOT-23 power MOSFET footprint. In converting this footprint to the pad set for a power device, designers must make two connections: an electrical connection and a thermal connection, to draw heat away from the package.

The electrical connections for the SOT-23 are very simple. Pin 1 is the gate, pin 2 is the source, and pin 3 is the drain. As in the other LITTLE FOOT packages, the drain pin serves the additional function of providing the thermal connection from the package to the PC board. The total cross section of a copper trace connected to the drain may be adequate to carry the current required for the application, but it may be inadequate thermally. Also, heat spreads in a circular fashion from the heat source. In this case the drain pin is the heat source when looking at heat spread on the PC board.

Figure 1 shows the footprint with copper spreading for the SOT-23 package. This pattern shows the starting point for utilizing the board area available for the heat spreading copper. To create this pattern, a plane of copper overlies the drain pin and provides planar copper to draw heat from the drain lead and start the process of spreading the heat so it can be dissipated into the

ambient air. This pattern uses all the available area underneath the body for this purpose.

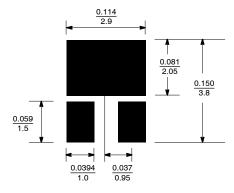


FIGURE 1. Footprint With Copper Spreading

Since surface-mounted packages are small, and reflow soldering is the most common way in which these are affixed to the PC board, "thermal" connections from the planar copper to the pads have not been used. Even if additional planar copper area is used, there should be no problems in the soldering process. The actual solder connections are defined by the solder mask openings. By combining the basic footprint with the copper plane on the drain pins, the solder mask generation occurs automatically.

A final item to keep in mind is the width of the power traces. The absolute minimum power trace width must be determined by the amount of current it has to carry. For thermal reasons, this minimum width should be at least 0.020 inches. The use of wide traces connected to the drain plane provides a low-impedance path for heat to move away from the device.



RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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